



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

DFNWB2*2-3L Plastic-Encapsulate Transistors

CJP718 TRANSISTOR (PNP)

FEATURE

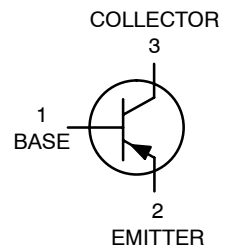
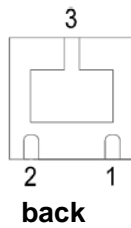
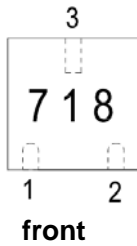
- Low Equivalent On Resistance
- Low Saturation Voltage

APPLICATIONS

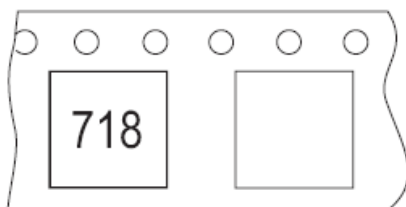
- DC-DC Converters (FET Driving)
- Charging Circuits
- Power Switches
- Motor Control



MARKING:



Tape Drawing (Unit : mm)



Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-20	
V_{EBO}	Emitter-Base Voltage	-7.5	
I_C	Collector Current-Continuous	-6	A
P_D	Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance. Junction to Ambient	125	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~+150	

Electrical characteristics (T_a=25°C unless otherwise noted)

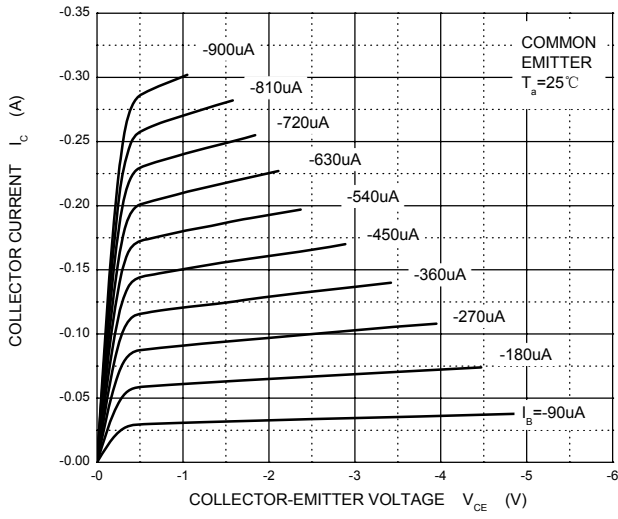
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-25			V
Collector-emitter breakdown voltage*	V _{(BR)CEO}	I _C =-10mA, I _B =0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-7.5			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V, I _E =0			-25	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V , I _C =0			-25	
DC current gain*	h _{FE}	V _{CE} =-2V, I _C =-10mA	300			
		V _{CE} =-2V, I _C =-100mA	300			
		V _{CE} =-2V, I _C =-2A	150			
		V _{CE} =-2V, I _C =-6A	15			
Collector-emitter saturation voltage*	V _{CE(sat)}	I _C =-0.1A, I _B =-10mA			-30	mV
		I _C =-1A, I _B =-20mA			-220	
		I _C =-1.5A, I _B =-50mA			-250	
		I _C =-2.5A, I _B =-150mA			-350	
		I _C =-3.5A, I _B =-350mA			-300	
Base-emitter turn-on voltage*	V _{BE(on)}	V _{CE} =-2V, I _C =-3.5A			-0.95	V
Base-emitter saturation voltage*	V _{BE(sat)}	I _B =-350mA, I _C =-3.5A			-1.075	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA, f=100MHz	150			MHz
Turn-on time	t _{on}	V _{CB} =-10V, I _C =-1A,		40		ns
Turn-off time	t _{off}	I _{B1} = I _{B2} =-10mA		670		

* Pulse Test : Pulse width≤300μs, duty cycle ≤2%.

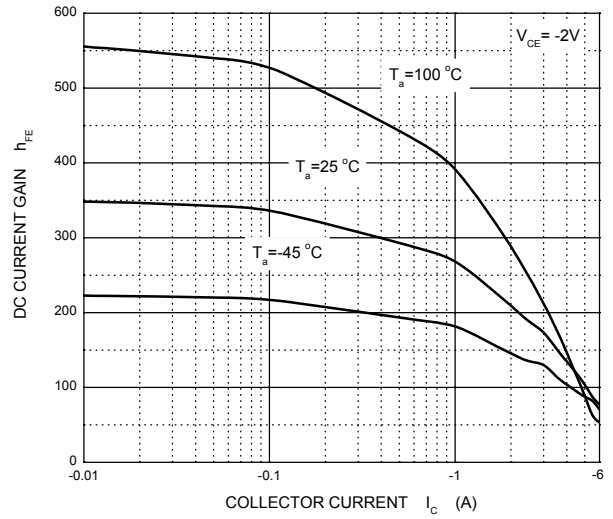
Typical Characteristics

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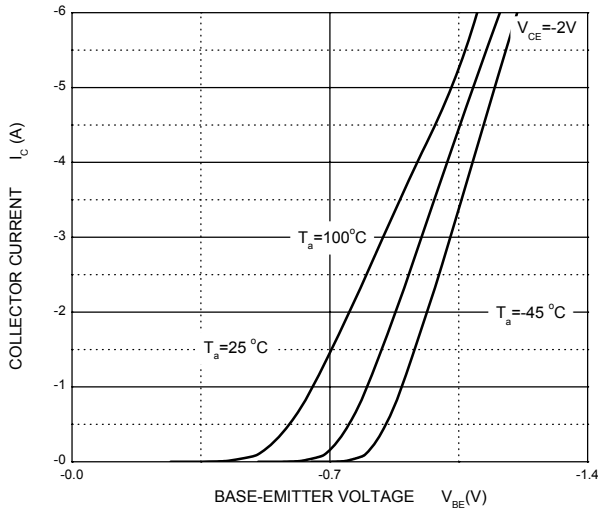
Static Characteristic



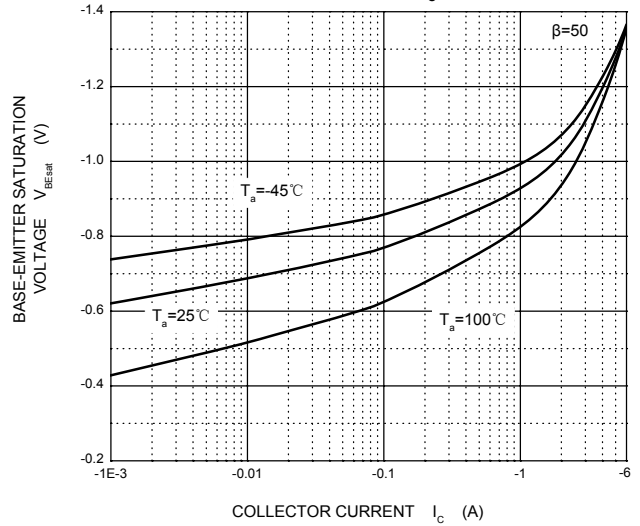
h_{FE} — I_c



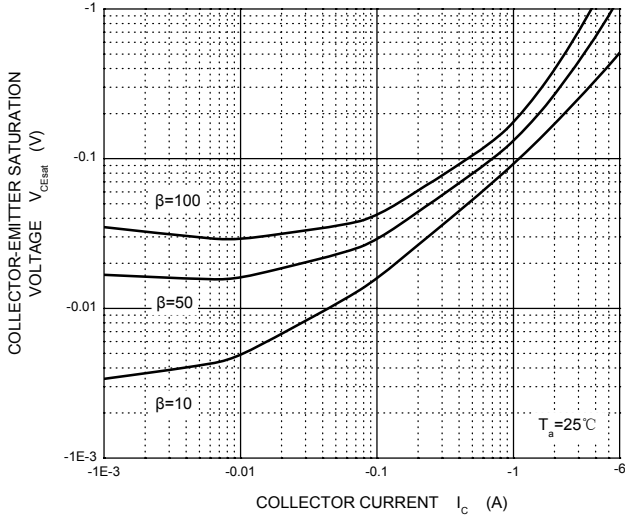
V_{BE} — I_c



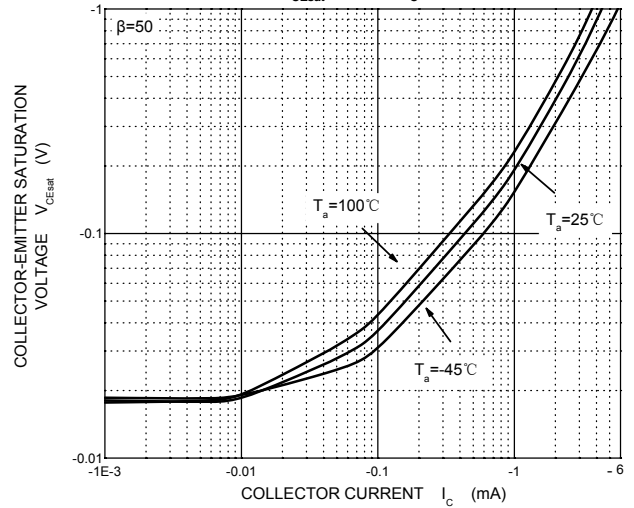
V_{BEsat} — I_c



V_{CEsat} — I_c



V_{CEsat} — I_c



Typical Characteristics

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